Abstract

The semiconductor device including an active pattern on a substrate and extending in a first direction, a gate structure on the active pattern, including a gate electrode extending in a second direction different from the first direction, a source/drain pattern on at least one side of the gate structure, and a source/drain contact on the source/drain pattern and connected to the source/drain pattern, wherein with respect to an upper surface of the active pattern, a height of an upper surface of the gate electrode is same as a height of an upper surface of the source/drain contact, and the source/drain contact comprises a lower source/drain contact and an upper source/drain contact on the lower source/drain contact, may be provided.

FIG. 2